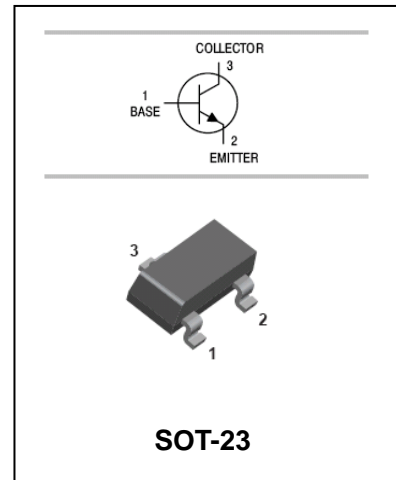


Silicon Epitaxial Planar Transistor

2SC3125

FEATURES

- Good Linearity of f_T .



ORDERING INFORMATION

Type No.	Marking	Package Code
2SC3125	HH	SOT-23

MAXIMUM RATING @ $T_a=25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	30	V
V_{CEO}	Collector-Emitter Voltage	25	V
V_{EBO}	Emitter-Base Voltage	4	V
I_C	Collector Current -Continuous	50	mA
I_B	Base Current	25	mA
P_C	Collector Dissipation	150	mW
T_j, T_{stg}	Junction and Storage Temperature	-55 to +125	$^\circ\text{C}$

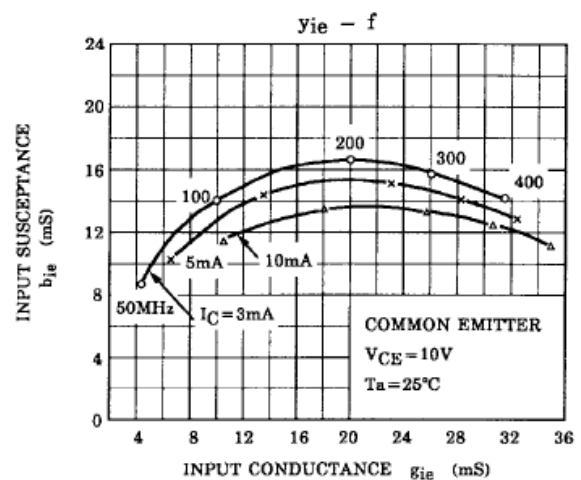
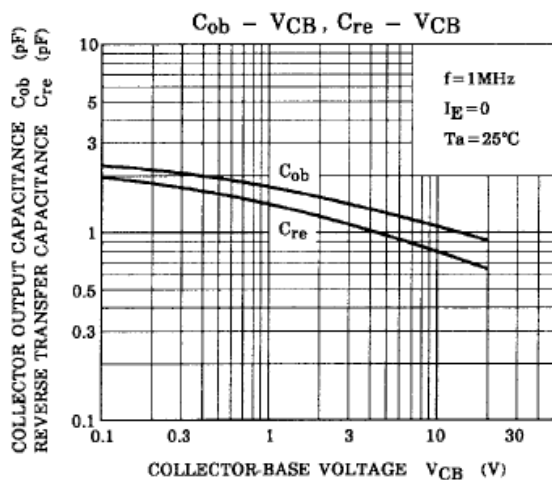
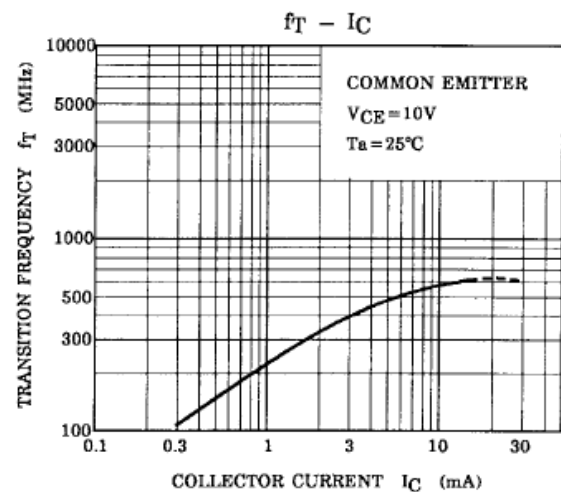
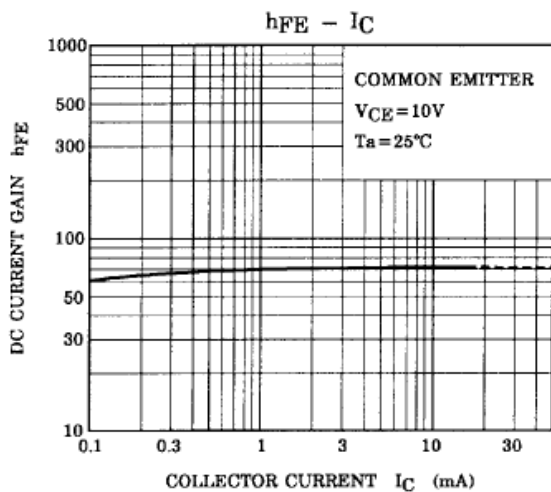
Silicon Epitaxial Planar Transistor

2SC3125

ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=10mA, I_B=0$	25			V
Collector cut-off current	I_{CBO}	$V_{CB}=30V, I_E=0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=3V, I_C=0$			0.1	μA
DC current gain	h_{FE}	$V_{CE}=10V, I_C=10mA$	20	70	200	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=15mA, I_B=1.5mA$			0.2	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=15mA, I_B=1.5mA$			1.5	V
Transition frequency	f_T	$V_{CE}=10V, I_C=10mA$	250	600		MHz
Collector-base output capacitance	C_{ob}	$V_{CB}=10V, I_E=0, f=1MHz$		1.1	1.6	MHz

TYPICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified



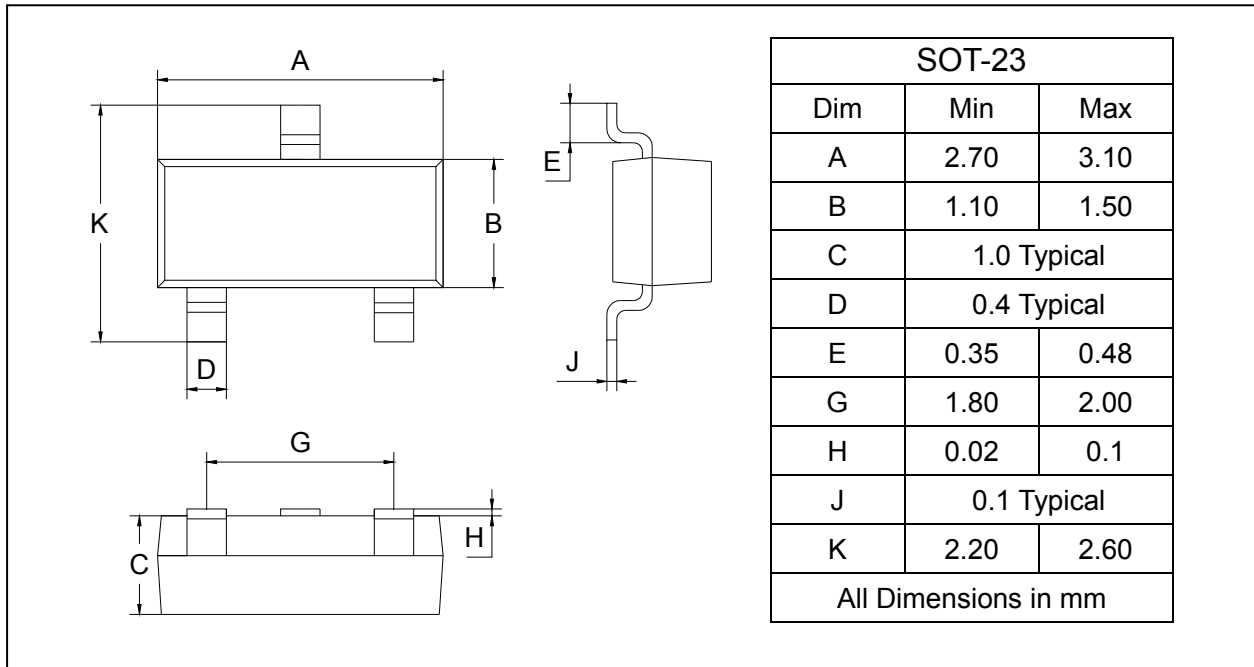
Silicon Epitaxial Planar Transistor

2SC3125

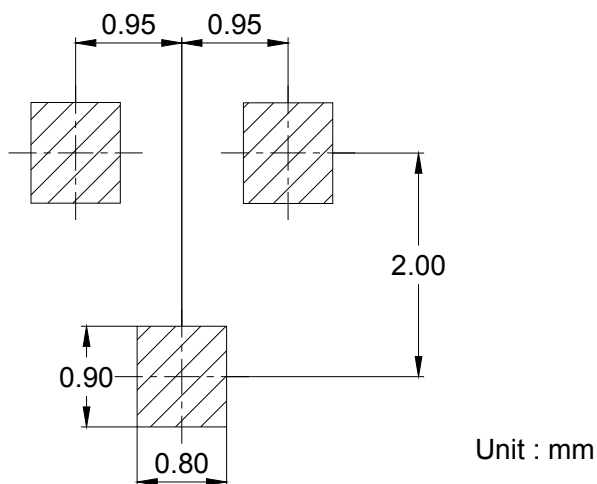
PACKAGE OUTLINE

Plastic surface mounted package

SOT-23



SOLDERING FOOTPRINT



PACKAGE INFORMATION

Device	Package	Shipping
2SC3125	SOT-23	3000/Tape&Reel